

A green rectangular road sign with a white border is mounted on a wooden post. The sign contains the text "The eGaN® FET Journey Continues". The background of the entire slide is a desert landscape with a road leading towards a building at sunset. The sky is blue with white clouds, and the sun is low on the horizon, creating a golden glow. The building in the distance has a grid-like facade.

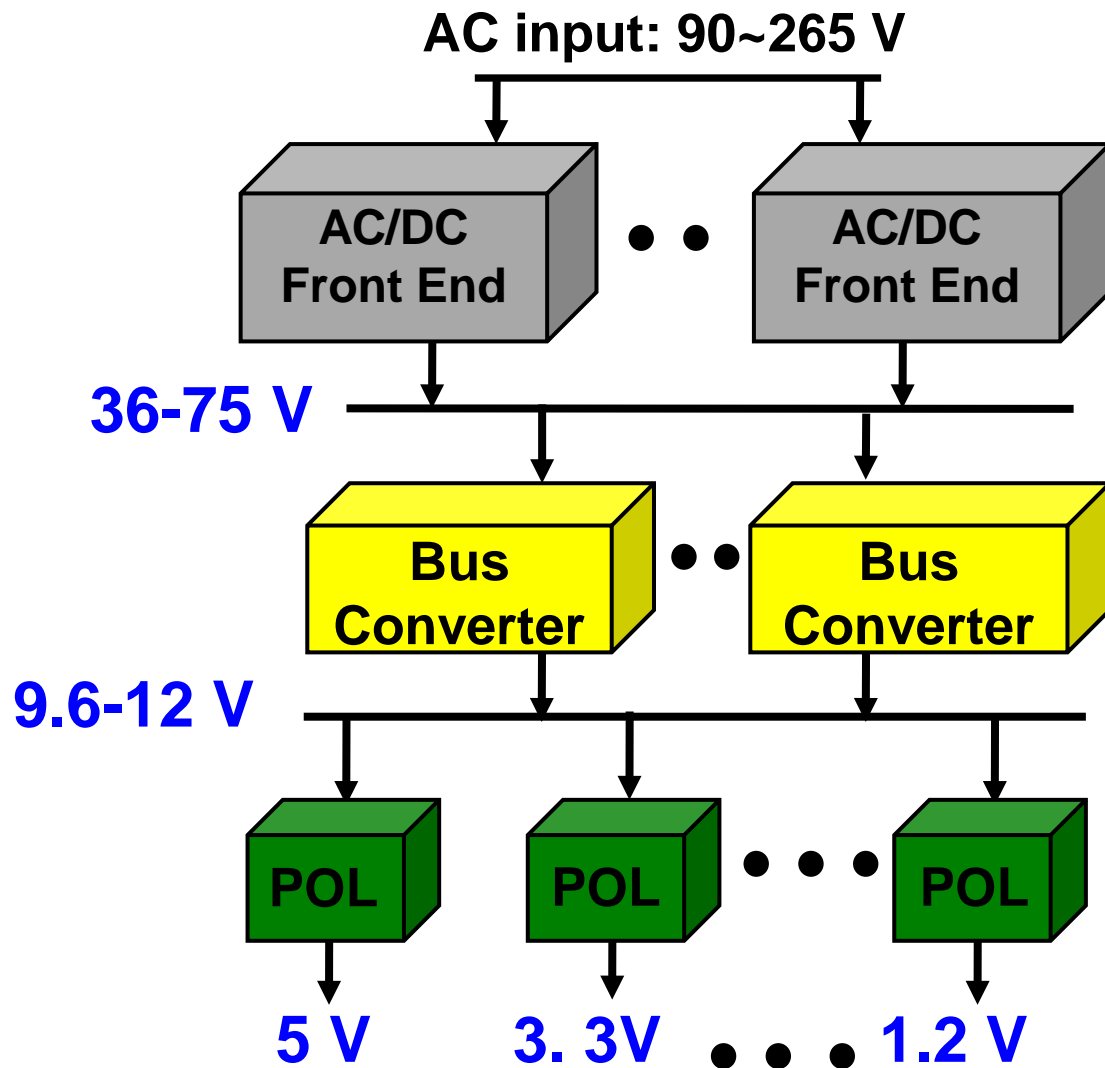
The eGaN® FET
Journey Continues

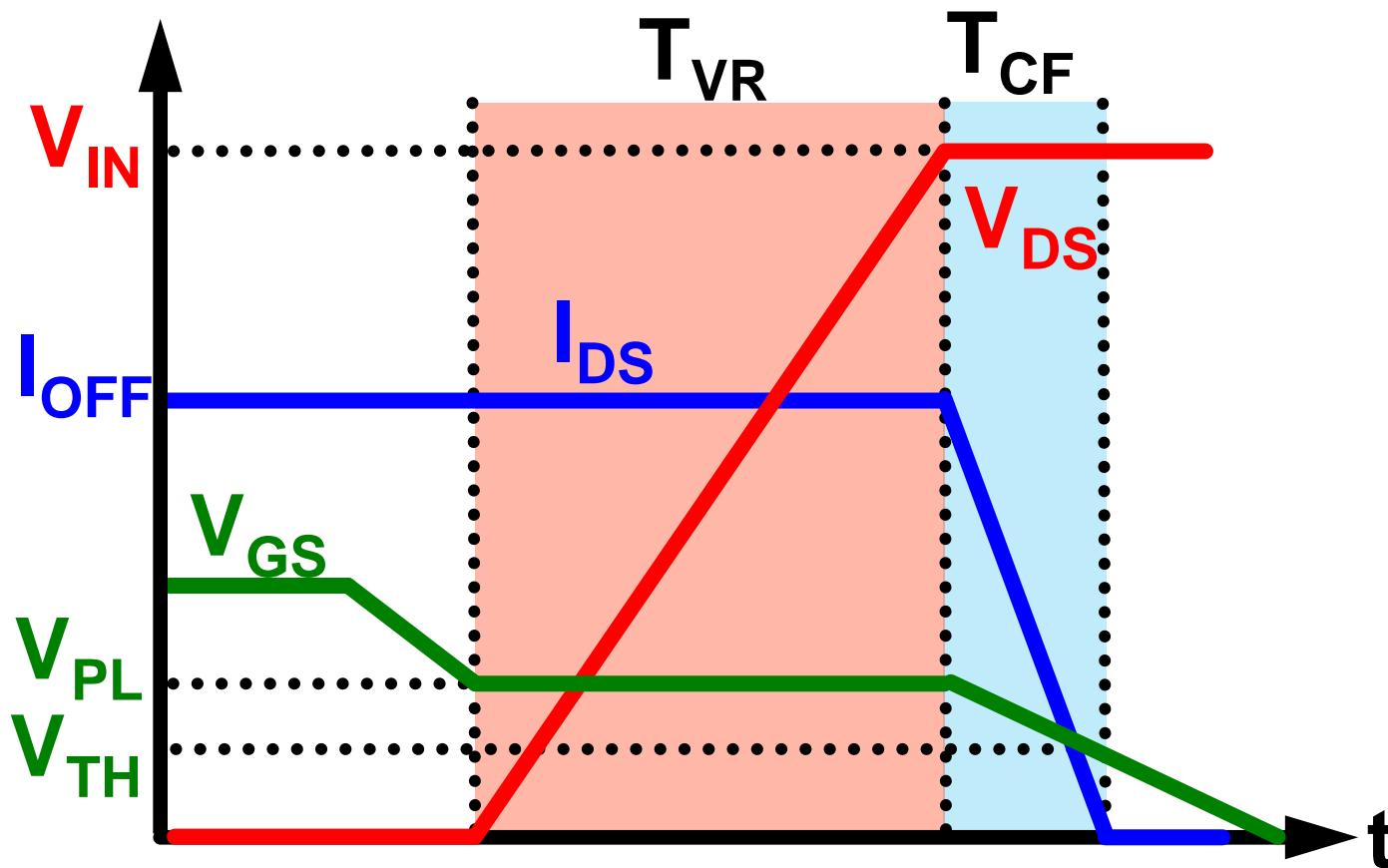
eGaN® FET Application: High Frequency Resonant Converters

David Reusch

Efficient Power Conversion Corporation

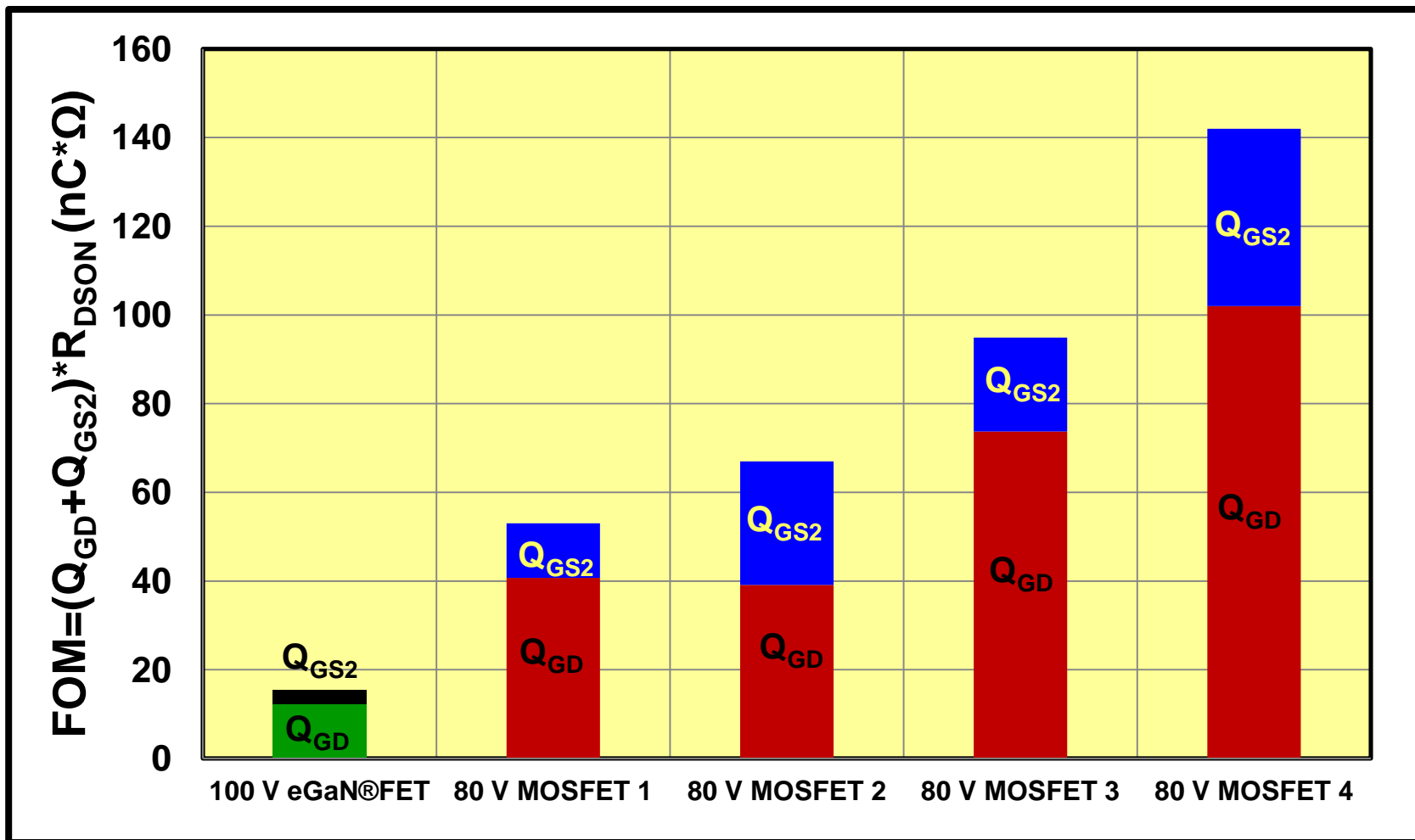
- **Overview of Power Architecture**
- **Hard Switching Converters with eGaN[®]FETs**
- **Soft Switching Converters with eGaN[®]FETs**
- **Summary**



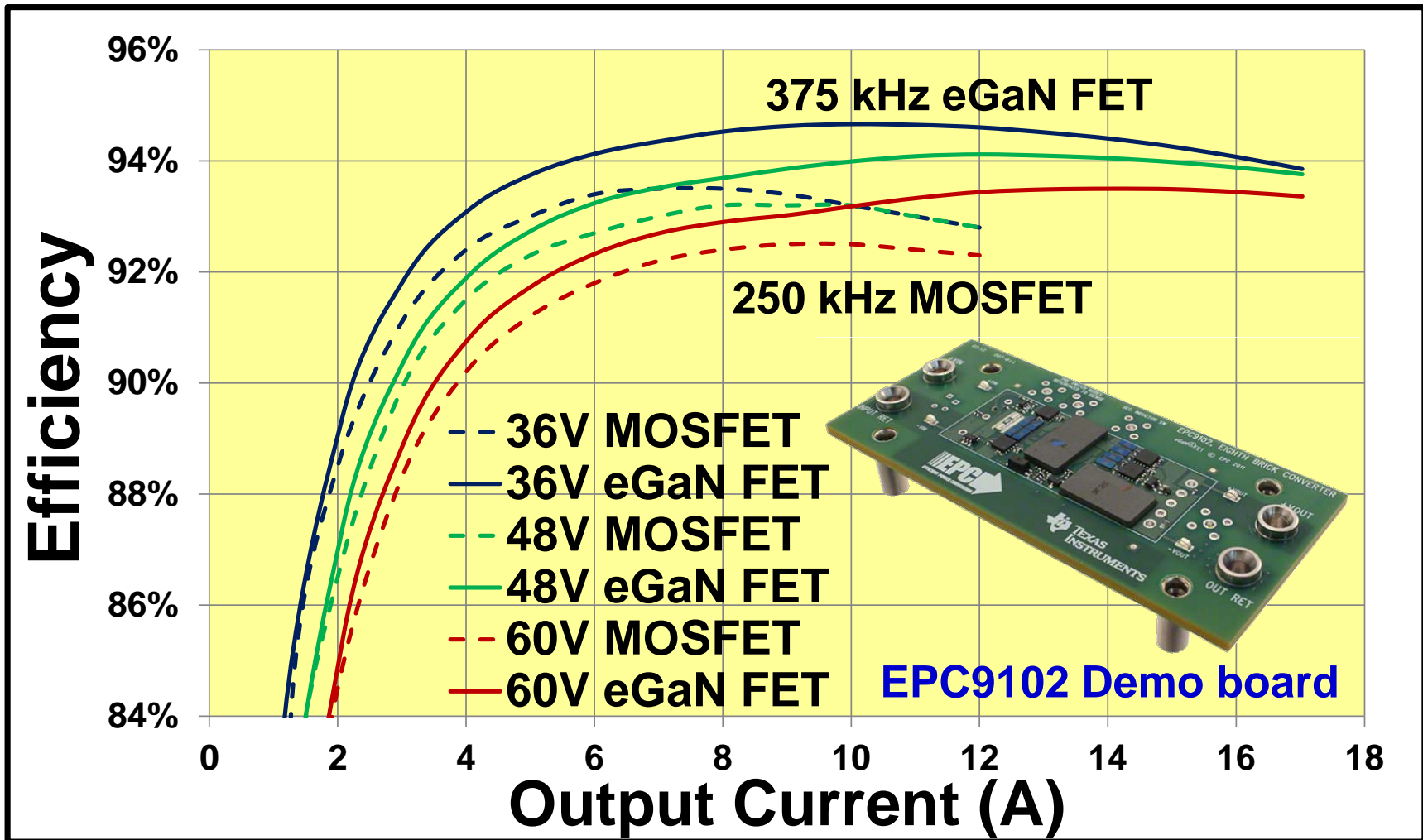


$$P_{T_{VR}} \approx \frac{V_{IN} * I_{OFF} * Q_{GD}}{2 * I_G}$$

$$P_{T_{CF}} \approx \frac{V_{IN} * I_{OFF} * Q_{GS2}}{2 * I_G}$$

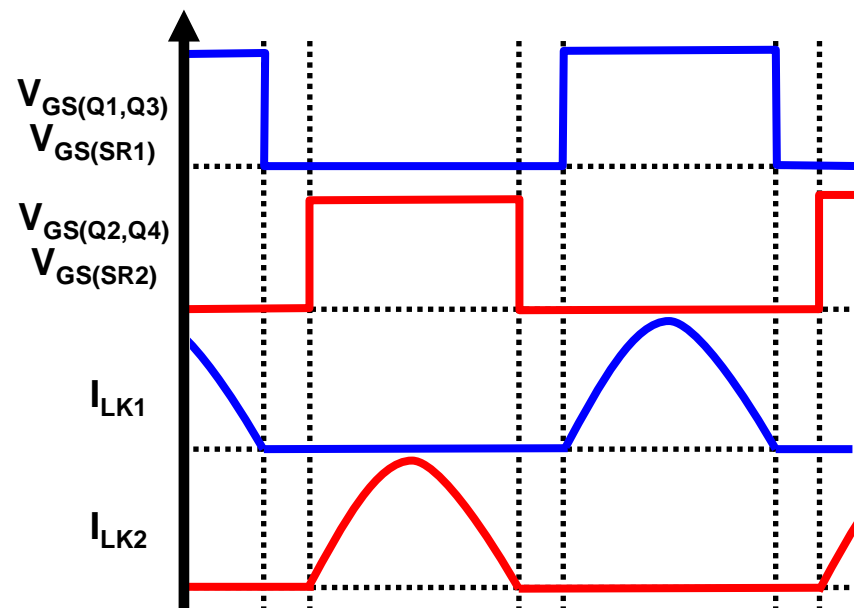
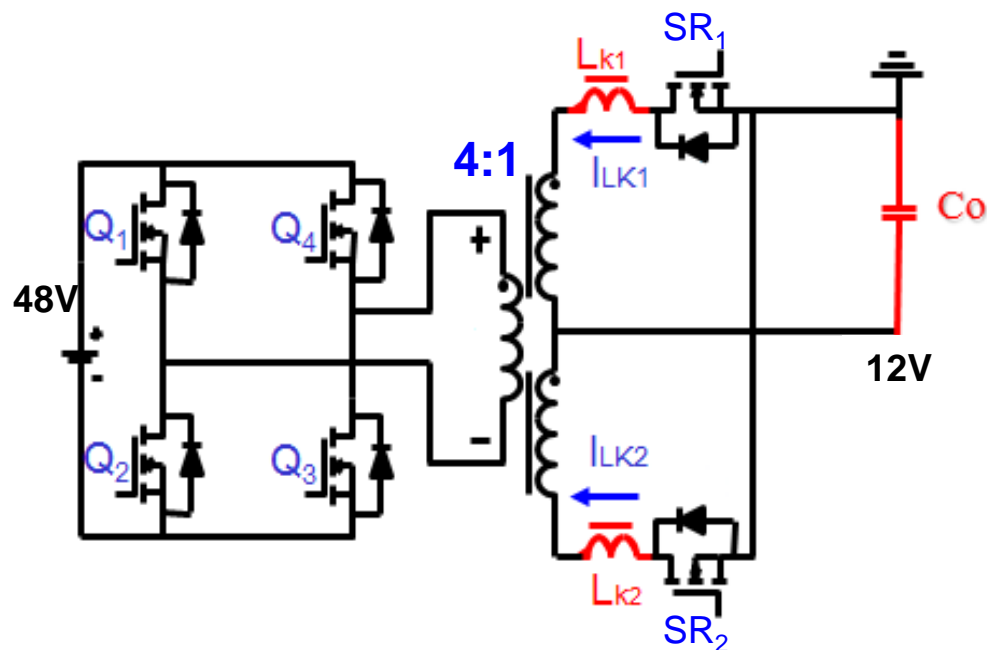


$$V_{DS} = 0.5 * V_{DS} , I_{DS} = 15 \text{ A}$$

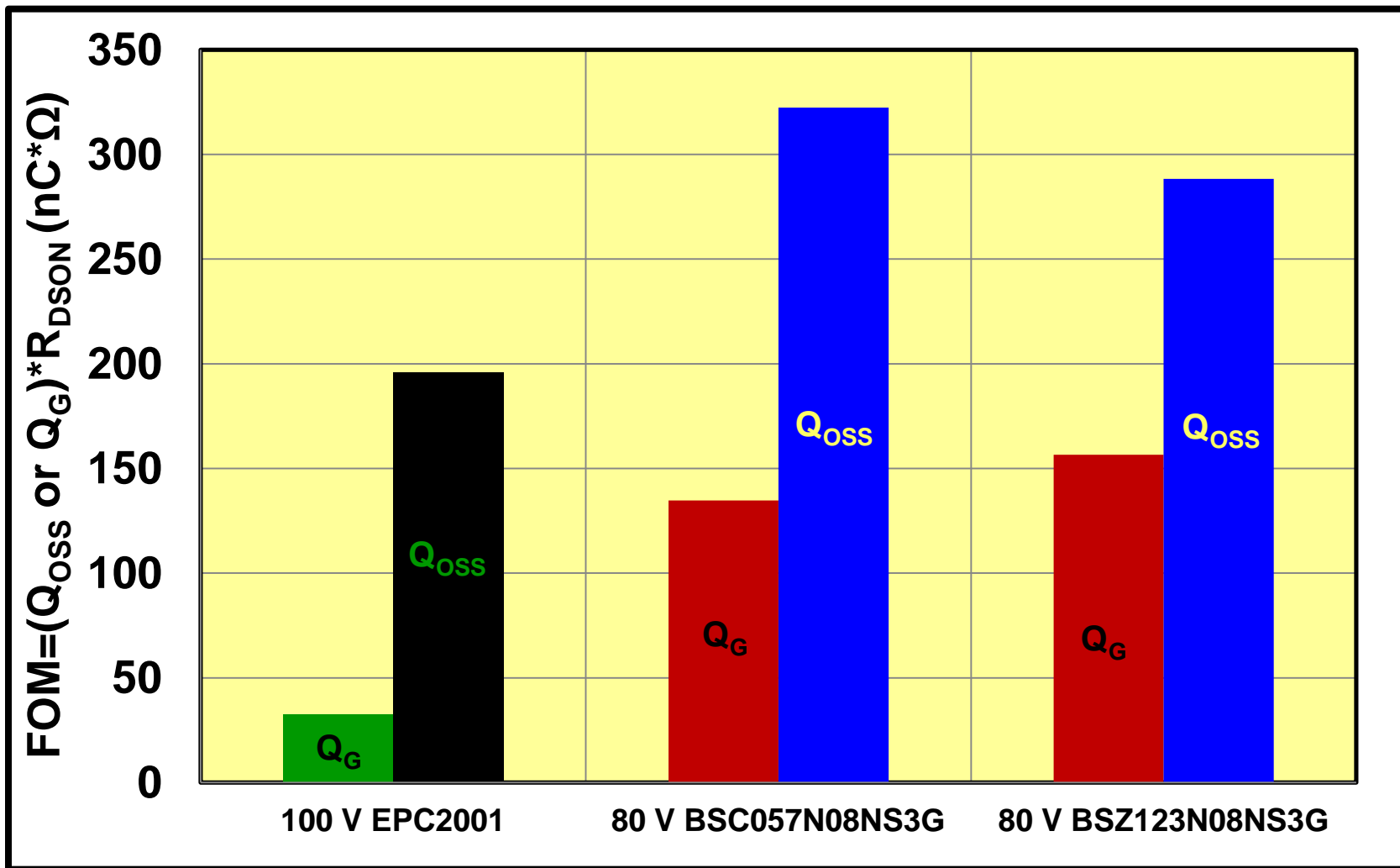


36 - 60 Vin, 12 Vout, 200 W, 375 kHz

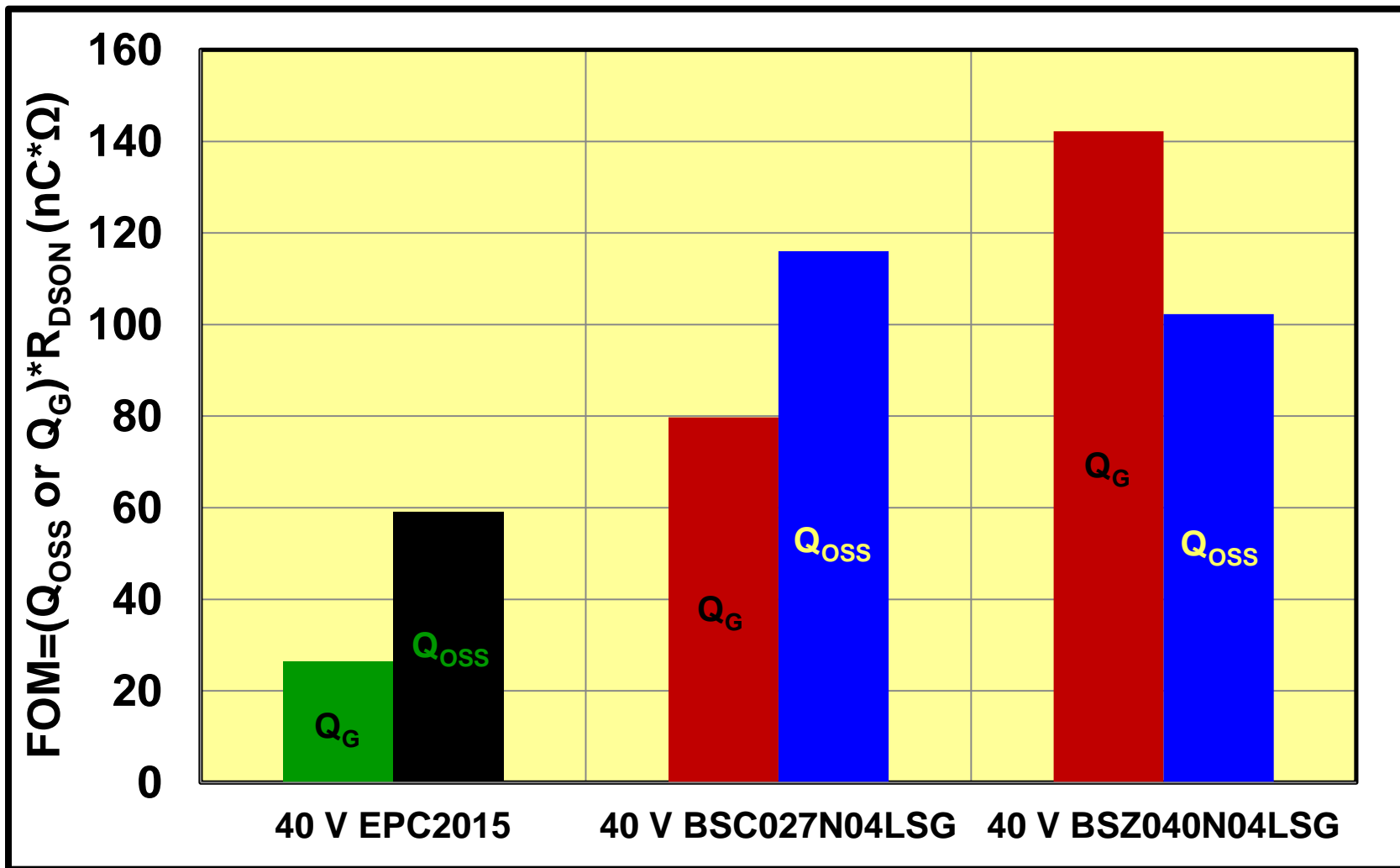
High Frequency DC/DC Transformer



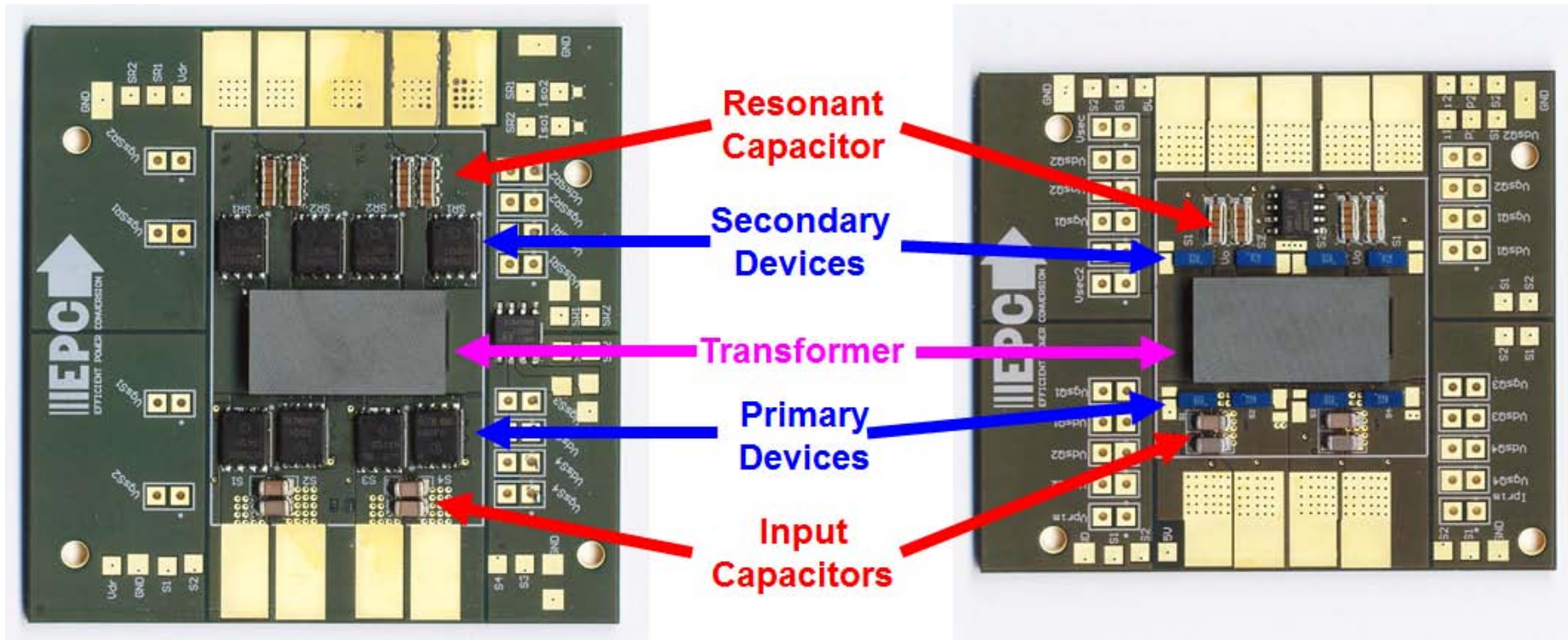
Ref: Y. Ren, M. Xu, J. Sun, and F. C. Lee, "A family of high power density unregulated bus converters," IEEE Trans. Power Electron., vol. 20, no. 5, pp. 1045–1054, Sep. 2005.



V_{DS} = 48 V



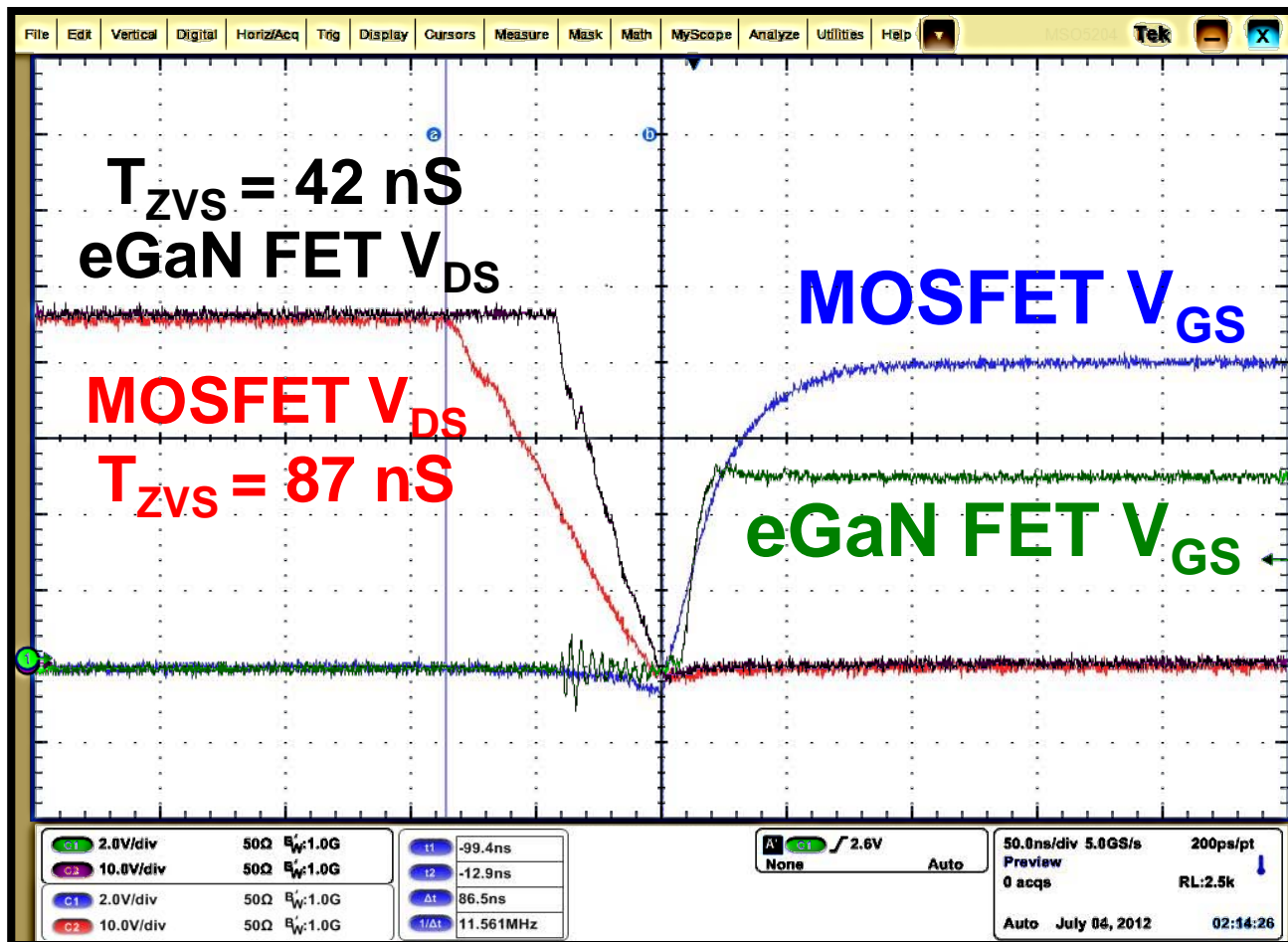
V_{DS} = 48 V



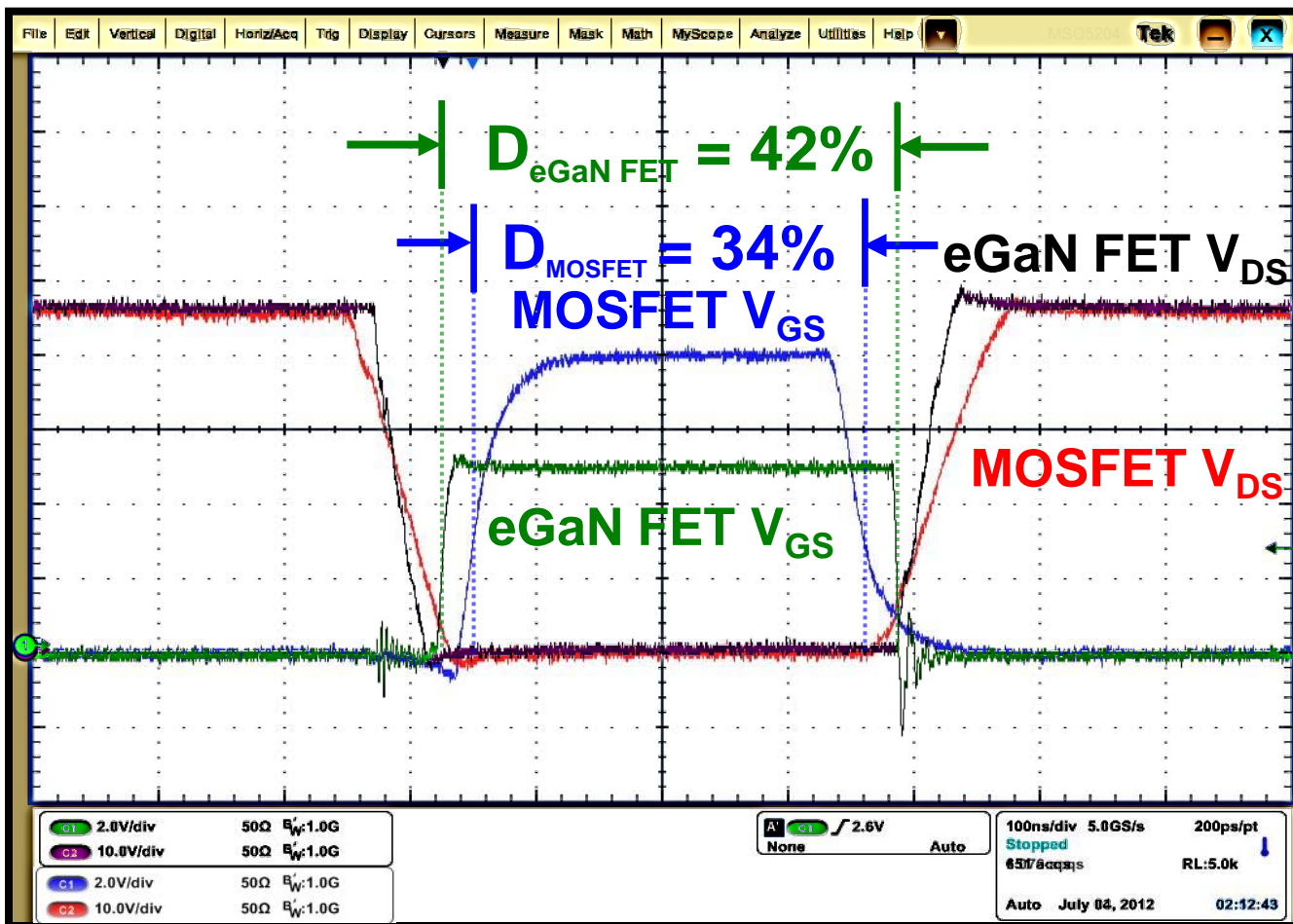
MOSFET

vs.

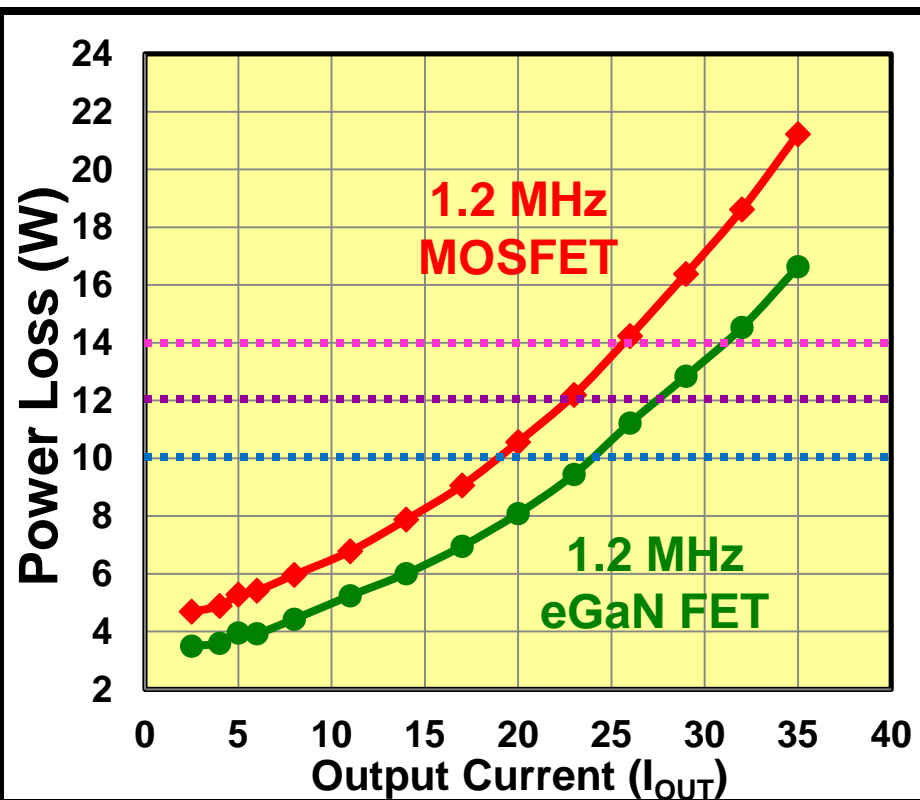
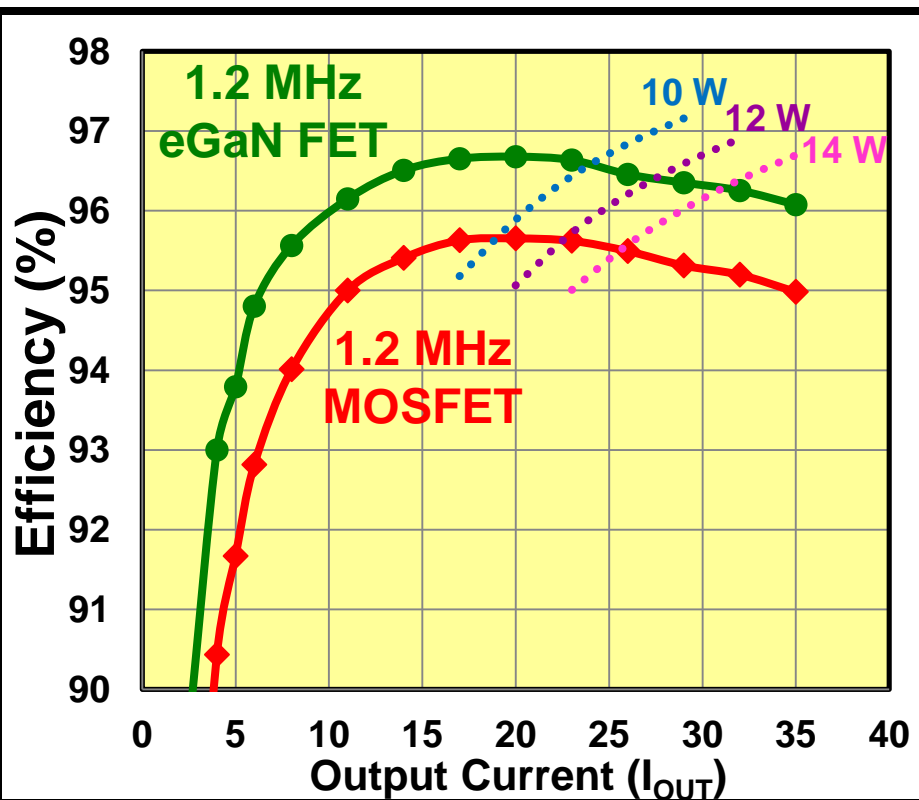
eGaN[®] FET



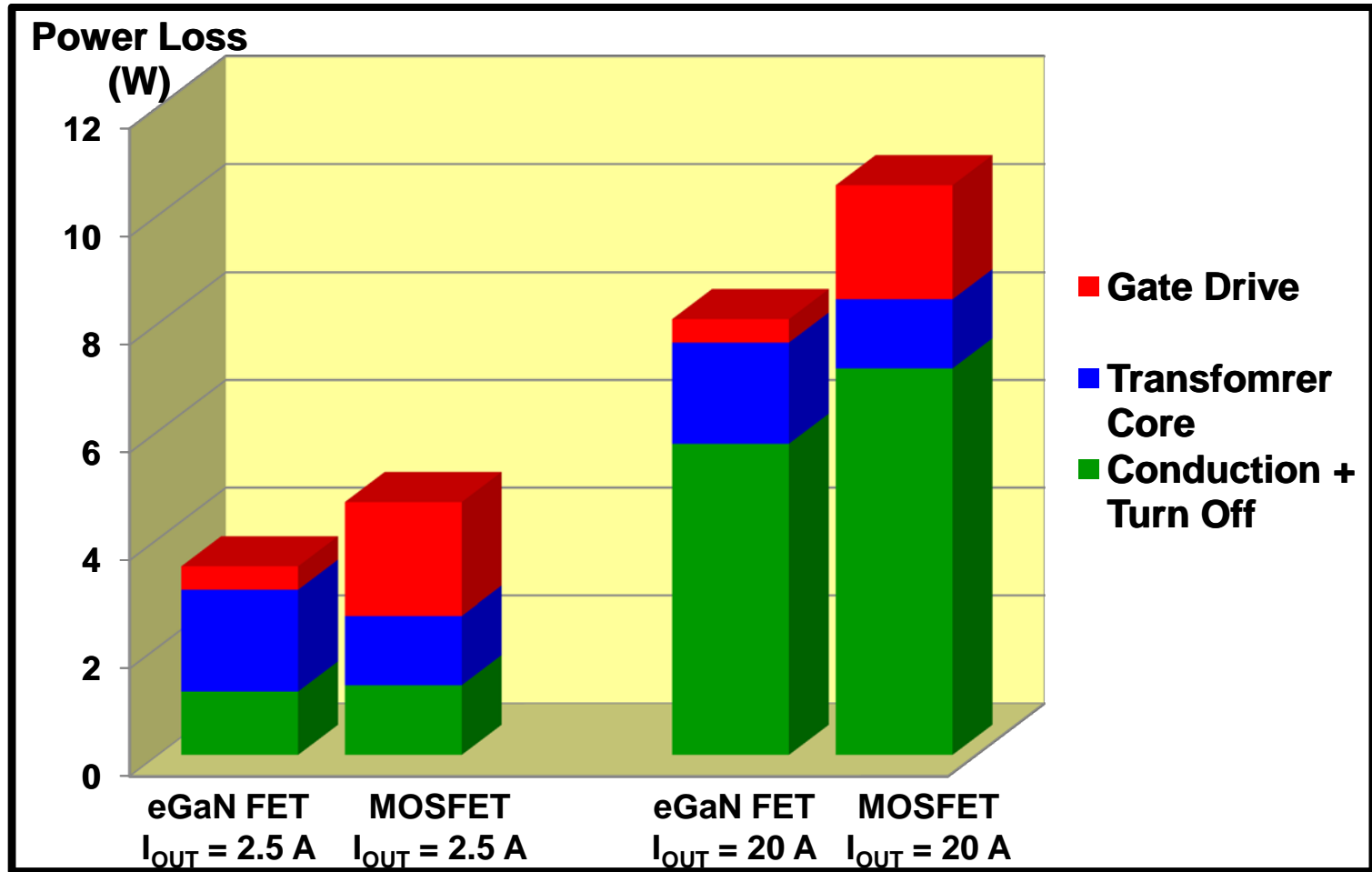
$F_S = 1.2 \text{ MHz}$, $V_{IN} = 48 \text{ V}$, and $V_{OUT} \approx 12 \text{ V}$



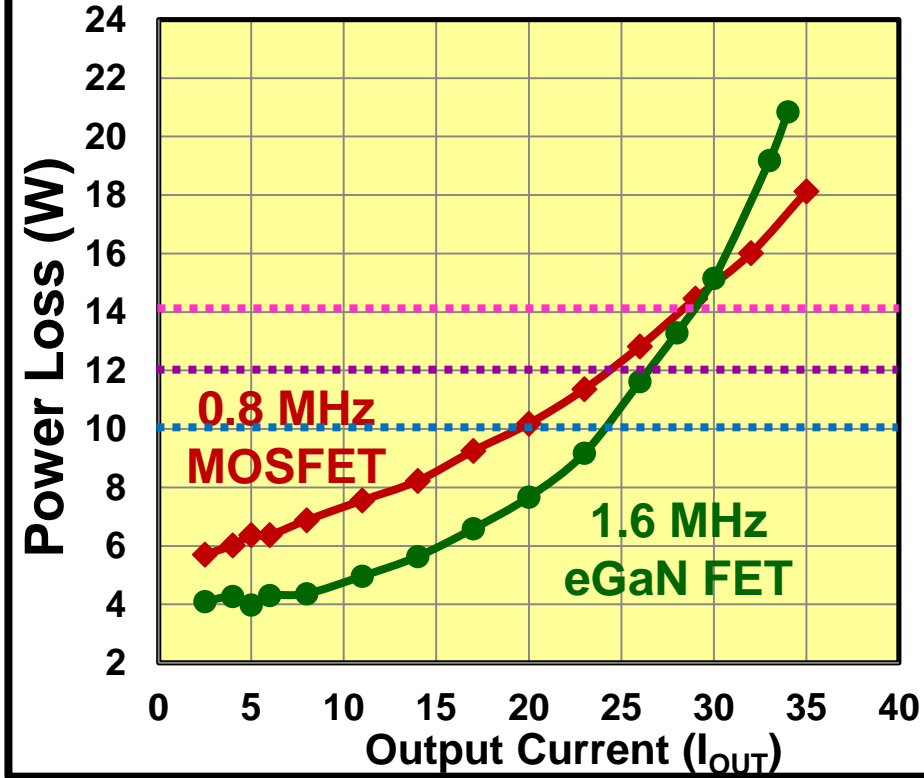
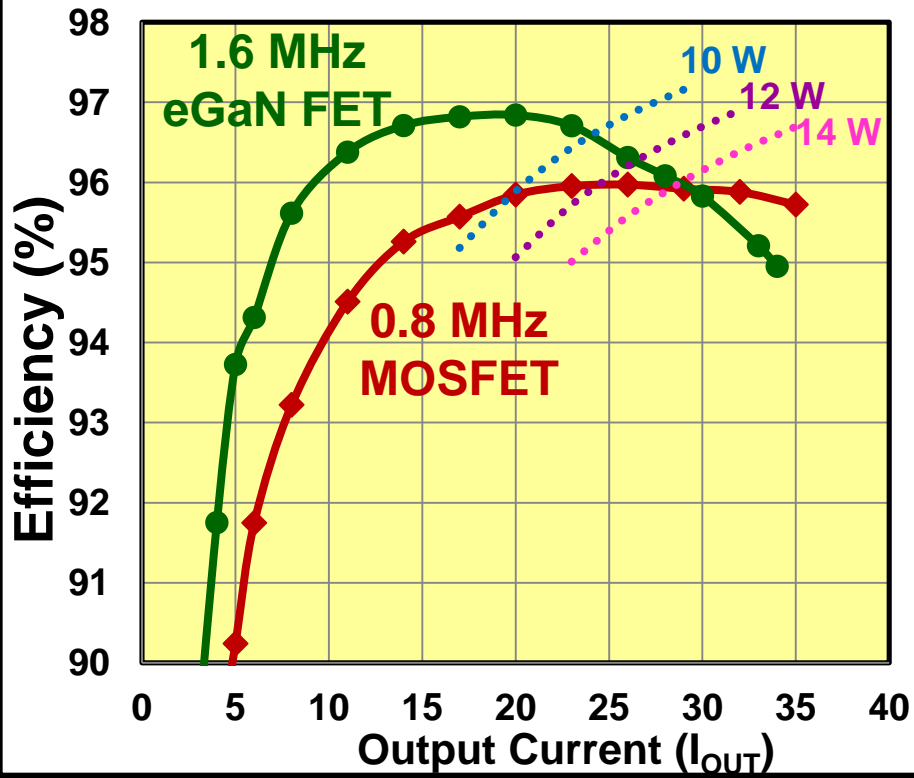
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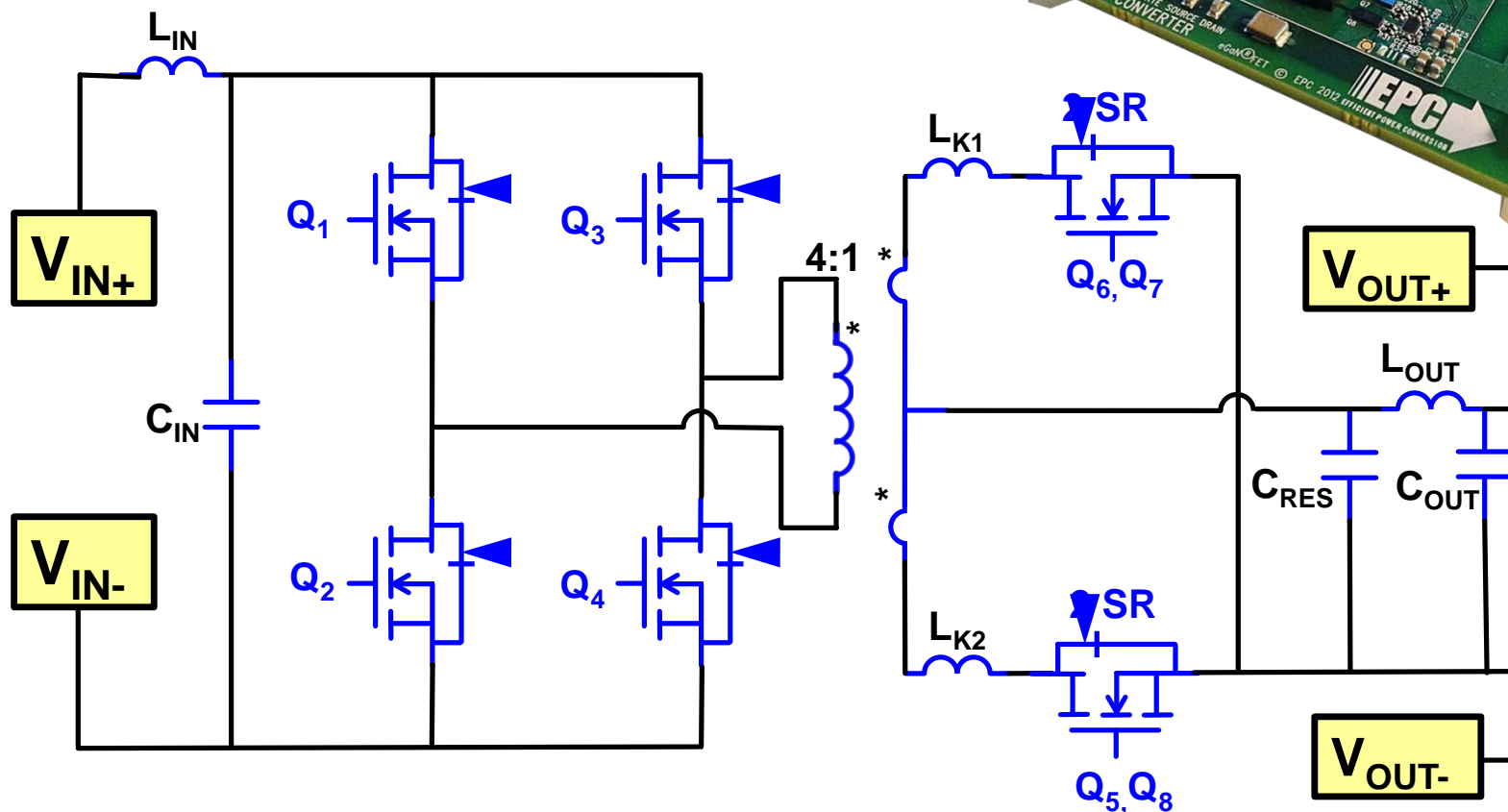
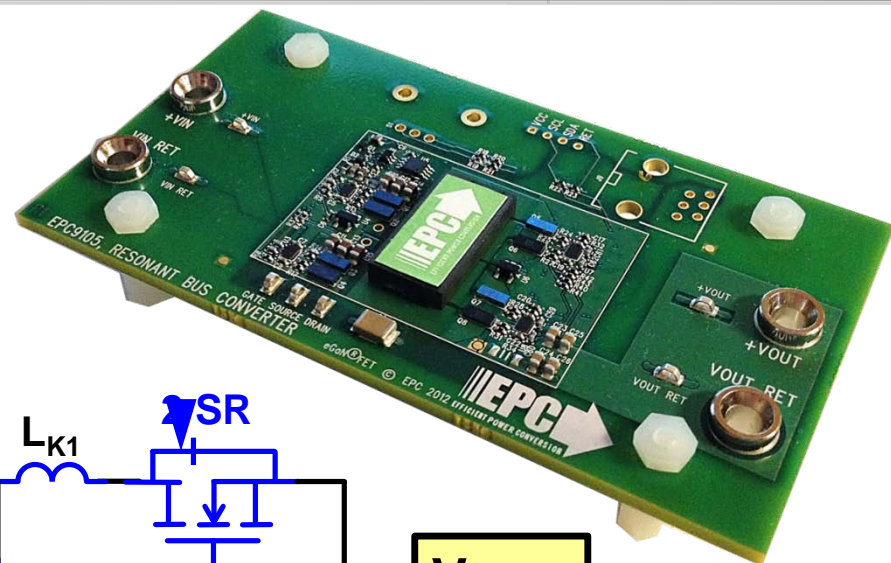
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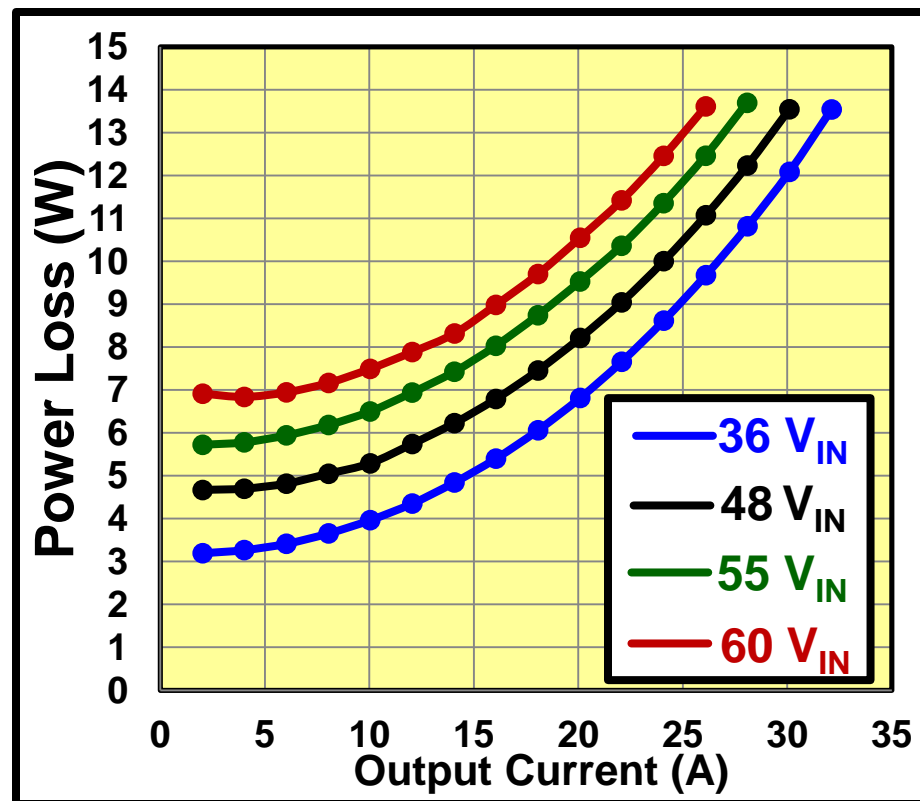
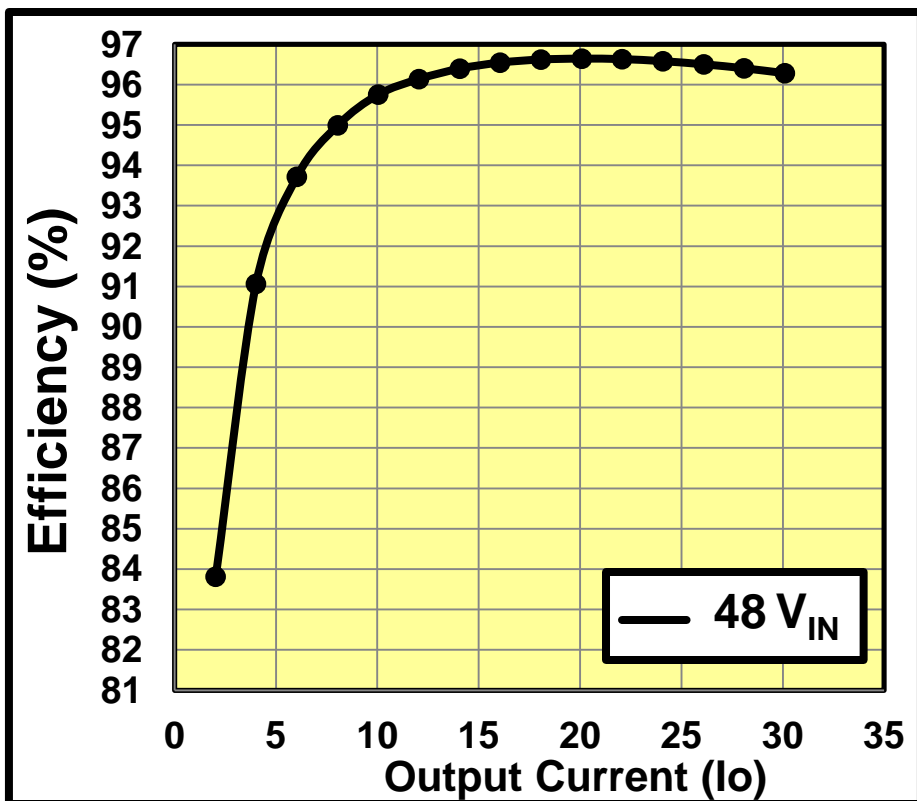


$V_{IN} = 48 \text{ V}$, and $V_{OUT} \approx 12 \text{ V}$

EPC9105 Demonstration Board

36 - 60 V_{IN}, 12 V_{OUT}, 350 W, 1.2 MHz





$F_S = 1.2 \text{ MHz}$, $V_{IN} = 36\text{-}60 \text{ V}$, and $V_{OUT} \approx V_{IN} / 4$

eGaN FETs improve high frequency resonant converter performance

- **Lower output charge**
- **Lower gate charge**
- **More power delivery per cycle**



*The end of the
road for silicon.....*

*is the beginning of
the eGaN FET
journey!*

